

ABSTRACT OF THE DISCLOSURE

In a method for forming a CVD-TiN film onto a tantalum oxide (Ta_2O_5) film, a substrate onto which a tantalum oxide film is formed is heated in the range from 500 °C to 700 °C in an atmosphere that does not react with the tantalum oxide film before the step of forming the CVD-TiN film onto the tantalum oxide film.

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